

14701 Firestone Blvd * La Mirada, Ca 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

DESIGNER'S DATA SHEET

Part Number / Ordering Information 1/ SDR9_UF ∟ Screening^{2/} = None TX = TX Level TXV = TXV Level S = S Level $_{-}$ = None L Package SMS = Surface Mount Square Tab **Recovery Time** UF = Ultra Fast Voltage J = 600 VK = 800 VM = 1000 V

SDR9JUF & UFSMS thru SDR9MUF & UFSMS

9 AMP 800-1000 Volts 70 nsec ULTRA FAST RECOVERY RECTIFIER

Features:

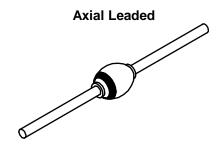
- Ultra Fast Recovery: 70 nsec maximum
- PIV to 1000 Volts
- Low Reverse Leakage Current
- Hermetically Sealed
- Single Chip Construction
- Replaces Larger DO-4 Rectifiers
- Low Thermal Resistance
- Fast and Hyper Fast Recovery Available. Contact Factory.
- TX, TXV, and S-Level Screening Available^{2/}

Maximum Ratings		Symbol	Value	Units	
DC Blocking Voltage	SDR9JUF & UFSMS SDR9KUF & UFSMS SDR9MUF & UFSMS	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	600 800 1000	Volts	
Average Rectified Forward Current (Resistive Load, 60 Hz Sine Wave, T _A = 25°C)		Io	9	Amps	
Repetitive Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on Io, Allow Junction to Reach Equilibrium Between Pulses, $T_A = 25^{\circ}\text{C}$)		I_{FSM}	125	Amps	
Operating & Storage Temperature		Top & Tstg	-65 to +175	°C	
Maximum Thermal Resistance Junction to Leads, L = .125 " (Axial Lead) Junction to End Tab (Surface Mount)		$R_{ heta m JL} \ R_{ heta m JE}$	8 4	°C/W	

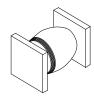
Notes:

1/ For Ordering Information, Price, Operating Curves, and Availability – Contact Factory.

2/ Screening Based on MIL-PRF-19500. Screening Flows Available on Request.







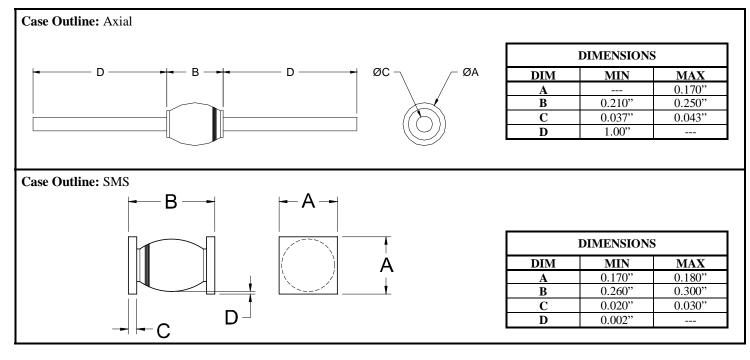


Solid State Devices, Inc.

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SDR9JUF & UFSMS thru SDR9MUF & UFSMS

Electrical Characteristics		Symbol	Min	Max	Units
Instantaneous Forward Voltage Drop (300-500 µs pulse)	$I_F = 3A, T_A = 25^{\circ}C$ $I_F = 9A, T_A = 25^{\circ}C$ $I_F = 9A, T_A = -55^{\circ}C$	$egin{array}{c} V_{F1} \ V_{F2} \ V_{F3} \end{array}$	 	1.50 1.90 2.10	Vdc
Reverse Leakage Current (Rated V _R , 300 µs pulse minimum)	$T_{A} = 25^{\circ}C$ $T_{A} = 100^{\circ}C$	$egin{array}{c} I_{R1} \ I_{R2} \end{array}$		10 250	μA
Junction Capacitance (V _R = 10 V, T _A = 25°C, f = 1MHz)		$\mathbf{C}_{\mathbf{J}}$		80	pF
Reverse Recovery Time $(I_F = 500 \text{ mA}, I_R = 1 \text{A}, I_{RR} = 0.25 \text{A}, T_A = 25 ^{\circ}\text{C})$		t_{rr}		70	nsec



Notes:

Consult manufacturing for operating curves.